

ABSTRACT OF THE DISCLOSURE

The invention includes a magnetoresistive memory device having a conductive core, and a first magnetic layer extending at least partially around the conductive core. A non-magnetic material is over at least a portion of the first magnetic layer and separated from the conductive core by at least the first magnetic layer. A second magnetic layer is over the non-magnetic material, and separated from the first magnetic layer by at least the non-magnetic material. The invention also includes methods of forming magnetoresistive memory devices.